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IDS/Statement

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:
Mailloux, et al.

Serial No.: 08/984,560

Filed: December 3, 1997

For: BURST/PIPELINED EDO MEMORY DEVICE

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§ Group Art Unit: 2751
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§ Examiner: Kim, H.
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§ Atty. Docket: 95-0653.01
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INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant[s] respectfully request[s] that this Information Disclosure Statement be entered and that the references listed on the attached Form PTO-1449 be considered by the Examiner and made of record. As the references are cumulative from the parent, copies of the listed references are not enclosed.

In accordance with 37 C.F.R. § 1.97(b), this Information Disclosure Statement is not to be construed as a representation that a search has been made or that no other possible material information as defined in 37 C.F.R. § 1.56(a) exists.

The following references are submitted for the Examiner's review:

U.S. Patents

U.S. Patent No.	Issue Date	Inventor
5,357,469	10/94	Sommer et al.
5,268,865	12/93	Takasugi
4,618,947	10/86	Tran et al.
5,267,200	11/93	Tobita
4,344,156	08/82	Eaton et al.
4,707,811	11/87	Takemae et al.
4,649,522	03/87	Kirsch
4,603,403	07/86	Toda

4,567,579	01/86	Patel et al.
4,484,308	11/84	Lewandowski et al.
4,875,192	10/89	Matsumoto
4,685,089	08/87	Patel et al.
4,562,555	12/85	Ouchi et al.
4,575,825	03/86	Ozaki et al.
4,788,667	11/88	Nakano
5,392,239	02/95	Margulis et al.
5,379,261	01/95	Jones, Jr.
5,126,975	06/92	Handy et al.
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5,526,320	06/96	Zagar et al.
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5,369,622	11/94	McLaury
5,568,445	10/96	Park et al.

Other References

Rossini, Pentium, PCI-ISA, Chip Set"' Symphony Laboratories, entire book.

Micron Technology, Inc., "1995 DRAM Data Book" pp. 4-1 thru 4-42, 12/95

Samsung Electronics, "Samsung Synchronous DRAM", March 1993, pgs. 1-16

Oki Electric Ind. Co., Ltd., "Burst DRAM Function & Pinout", 2nd presentation, Item #619, September, 1994

Toshiba America Electronic Components, Inc., "Application Specific DRAM, 1994", Pgs. C-178, C-260, C218

Micron Semiconductor, Inc., "Synchronous DRAM 2 MEG x 8 SDRAM", Pgs. 2-43 through 2-83

Toshiba America Electronic Components, Inc., "4M DRAM 1991", Pgs. A-137 - A-159

Micron Semiconductor, Inc., "1994 DRAM Data Book", pgs. 2-1 to 2-6

Mosel-Vitelic V53C8257H DRAM Specification Sheet, 20 pgs.

Toshiba Corp., "Integrated Circuit Technical Data-262,144 Words x 8 Bits Multiport DRAM", TC52826TS/Z/FT/TR-1, TEN. Rev. 2.1

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Micron Technology, Inc., "1995 DRAM Data Book", Pgs. 3-1 to 3-37

"Hyper Page Mode DRAM", 8029 Electronic Engineering, 66, No. 813, Woolwich, London, GB, pp. 47-48, (September 1994)

Dave Bursky, "Novel I/O Options and Innovative Architectures Let DRAMs Achieve SRAM

Performance; Fast DRAMS can be swapped for SRAM Caches", Electronic Design, Vol. 41, No. 15, Cleveland, Ohio, pp. 55-67, (July 22, 1993)

Shiva P. Gowni, et al., "A 9NS, 32K X 9, BICMOS TTL Synchronous Cache RAM With Burst Mode

Access", IEEE, Cutsom Integrated Circuits Conference, pp. 781-786, (March 3, 1992)
S3 Incorporated, "S3 Burst Mode DRAM", 6/93, 2 pages

Electronic News "Mitsubishi Samples 16M Synch DRAM", 10/25/93, pgs. 3-4

""DRAM 1 Meg X 4 DRAM 5BEDO Page Mode",", 1995 DRAM Data Book, pp.1-1 thru 1-30, (Micron Technology, Inc.)

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Samsung Electronics "KM48SV2000 Preliminary CMOS SDRAM" Rev.1(Mar, 1993), pgs. 7-8

Related Co-pending Applications

PCT Patent Application No. PCT/US95/16656, filed 12/21/1995, entitled: Burst Edo Memory Device Address Counter.

PCT Patent Application No. PCT/US95/16984 , filed 12/22/1995, entitled: Burst Edo Memory Device.

As this information is being submitted within three months of the date of filing of the application, Applicant understands that no fee or certification is required for the submission and consideration of this information at this time.

If there are any matters which may be resolved or clarified through telephone interview, the Examiner is respectfully requested to contact Applicant's undersigned attorney at the number indicated.

* * * *

A Form PTO-1449 is enclosed herewith.

Date: 2-22-99

Respectfully submitted,

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